

## Power MOSFET

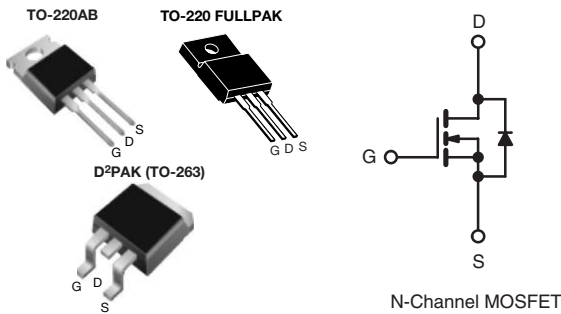
PRODUCT SUMMARY	
$V_{DS}$ (V) at $T_J$ max.	560 V
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10$ V   0.555
$Q_g$ (Max.) (nC)	48
$Q_{gs}$ (nC)	12
$Q_{gd}$ (nC)	15
Configuration	Single

### FEATURES

- Low Figure-of-Merit  $R_{on} \times Q_g$
- 100 % Avalanche Tested
- Gate Charge Improved
- $T_{rr}/Q_{rr}$  Improved
- Compliant to RoHS Directive 2002/95/EC



Available  
**RoHS\***  
COMPLIANT



ORDERING INFORMATION			
Package	TO-220AB	D <sup>2</sup> PAK (TO-263)	TO-220 FULLPAK
Lead (Pb)-free	SiHP12N50C-E3	SiHB12N50C-E3	SiHF12N50C-E3

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT		UNIT
		TO220-AB D <sup>2</sup> PAK (TO-263)	TO-220 FULLPAK	
Drain-Source Voltage	$V_{DS}$	500		V
Gate-Source Voltage	$V_{GS}$	$\pm 30$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$V_{GS}$ at 10 V	$T_C = 25^\circ\text{C}$	12	A
		$T_C = 100^\circ\text{C}$	7.5	
Pulsed Drain Current <sup>c</sup>	$I_{DM}$	28		
Linear Derating Factor		1.67	0.28	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	180		mJ
Maximum Power Dissipation	$P_D$	208	36	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150		$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) <sup>d</sup>	for 10 s	300		

### Notes


- Limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25^\circ\text{C}$ ,  $L = 2.5$  mH,  $R_g = 25 \Omega$ ,  $I_{AS} = 12$  A.
- Repetitive rating; pulse width limited by maximum junction temperature.
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TO220-AB D <sup>2</sup> PAK (TO-263)	TO-220 FULLPAK	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	62	65	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	0.6	3.5	
Junction-to-Ambient (PCB mount) <sup>a</sup>	$R_{thJA}$	40	-	

**Note**

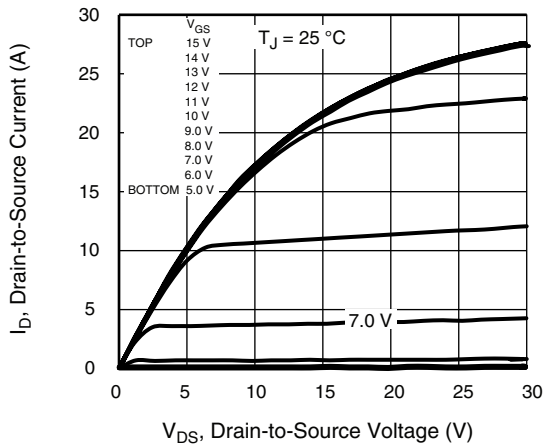
a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.6	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		3.0	-	5.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	50	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4\text{ A}$	-	0.46	0.555	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 3\text{ A}$		-	3	-	S
Dynamic							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$		-	1375	-	$\mu\text{F}$
Output Capacitance	$C_{oss}$			-	165	-	
Reverse Transfer Capacitance	$C_{rss}$			-	17	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, V_{DS} = 400\text{ V}$	-	32	48	nC
Gate-Source Charge	$Q_{gs}$			-	12	-	
Gate-Drain Charge	$Q_{gd}$			-	15	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 10\text{ A}, R_g = 4.3\text{ }\Omega, V_{GS} = 10\text{ V}$		-	18	-	ns
Rise Time	$t_r$			-	35	-	
Turn-Off Delay Time	$t_{d(off)}$			-	23	-	
Fall Time	$t_f$			-	6	-	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{open drain}$		-	1.1	-	$\Omega$
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	12	A
Pulsed Diode Forward Current	$I_{SM}$			-	-	28	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 10\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.8	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S, dI/dt = 100\text{ A}/\mu\text{s}, V_R = 20\text{ V}$		-	580	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	4.3	-	$\mu\text{C}$
Body Diode Reverse Recovery Current	$I_{RRM}$			-	13	-	A

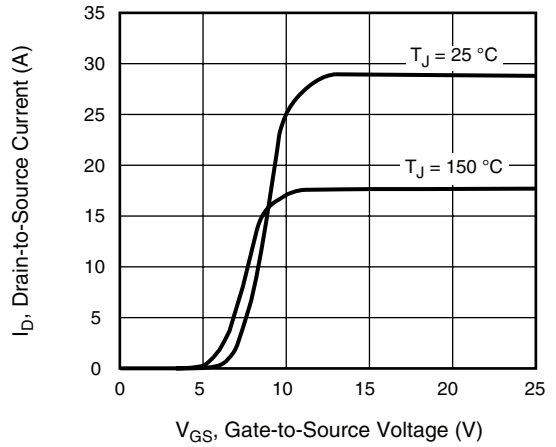
**Note**

- The information shown here is a preliminary product proposal, not a commercial product data sheet. Vishay Siliconix is not committed to produce this or any similar product. This information should not be used for design purposes, nor construed as an offer to furnish or sell such products.

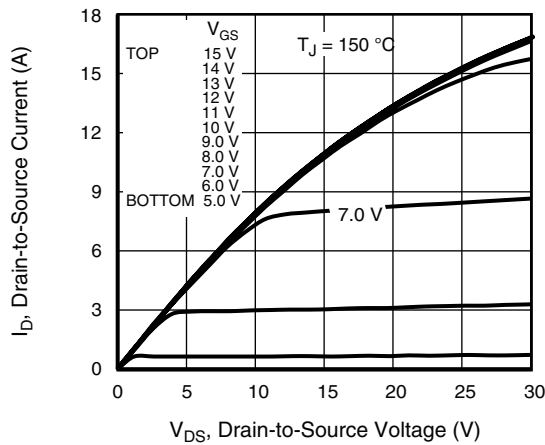
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



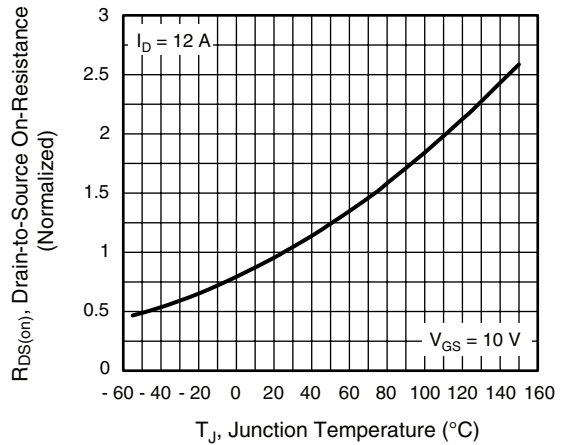
**Fig. 1 - Typical Output Characteristics (TO-220)**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 2 - Typical Output Characteristics (TO-220)**



**Fig. 4 - Normalized On-Resistance vs. Temperature**

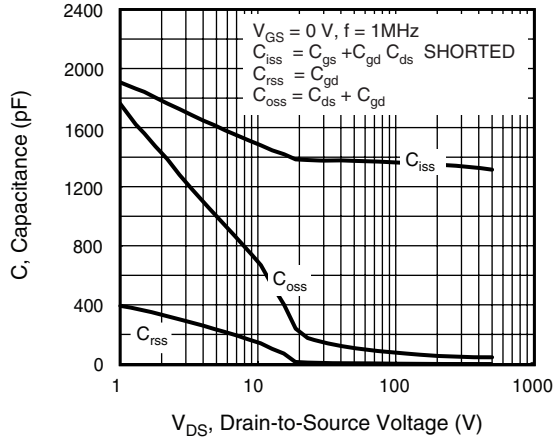


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

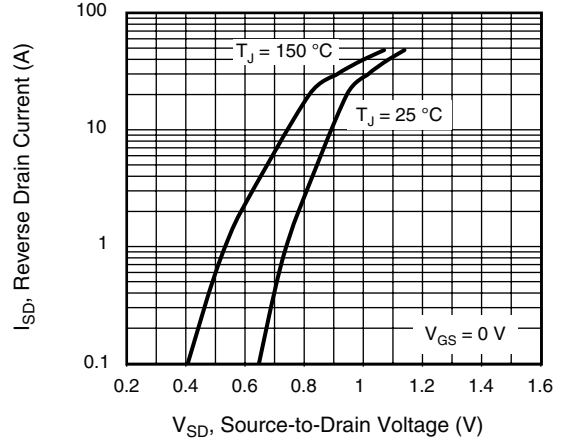


Fig. 7 - Typical Source-Drain Diode Forward Voltage

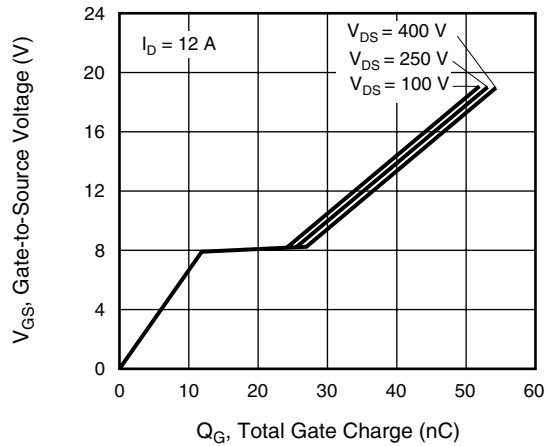


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

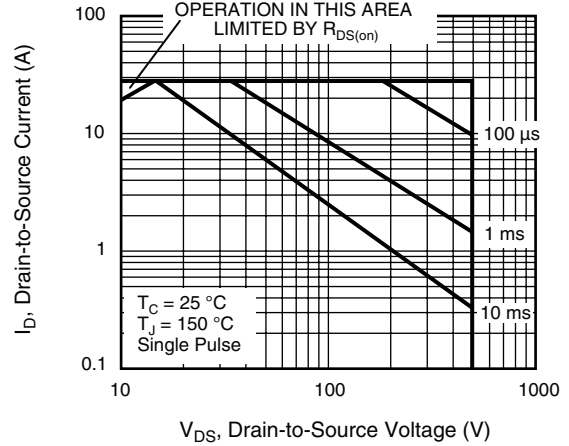


Fig. 8 - Maximum Safe Operating Area (TO-220AB, D2PAK)

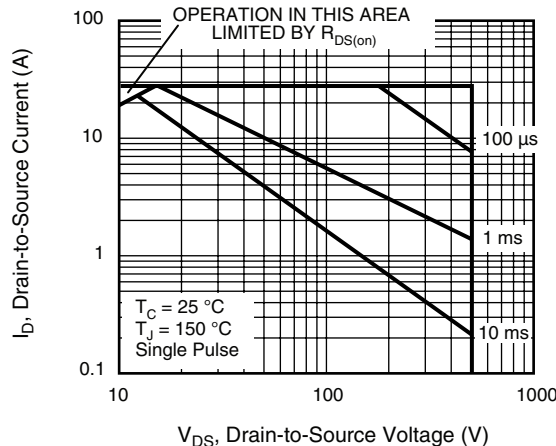
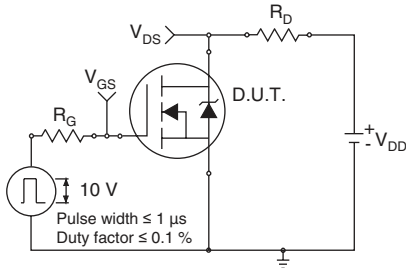
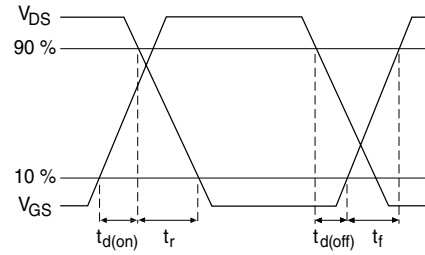


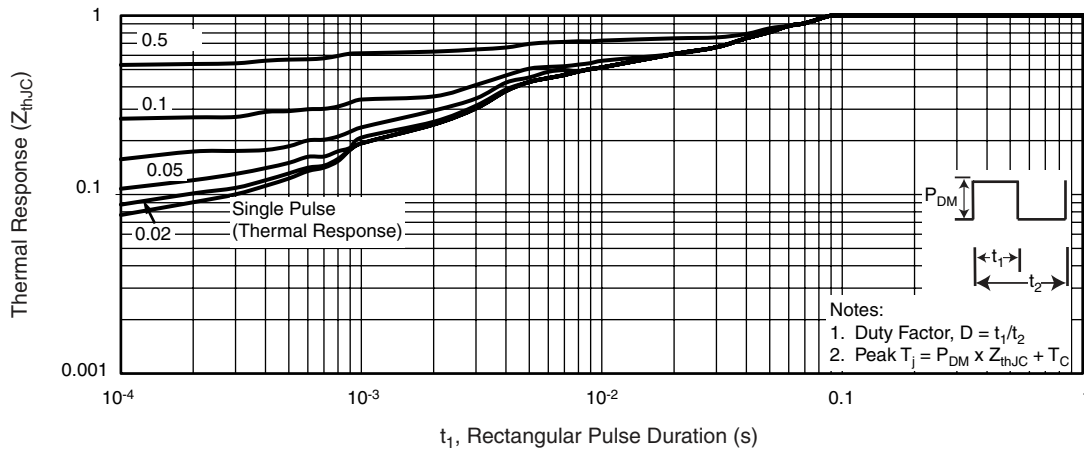
Fig. 9 - Maximum Safe Operating Area (TO-220 FULLPAK)



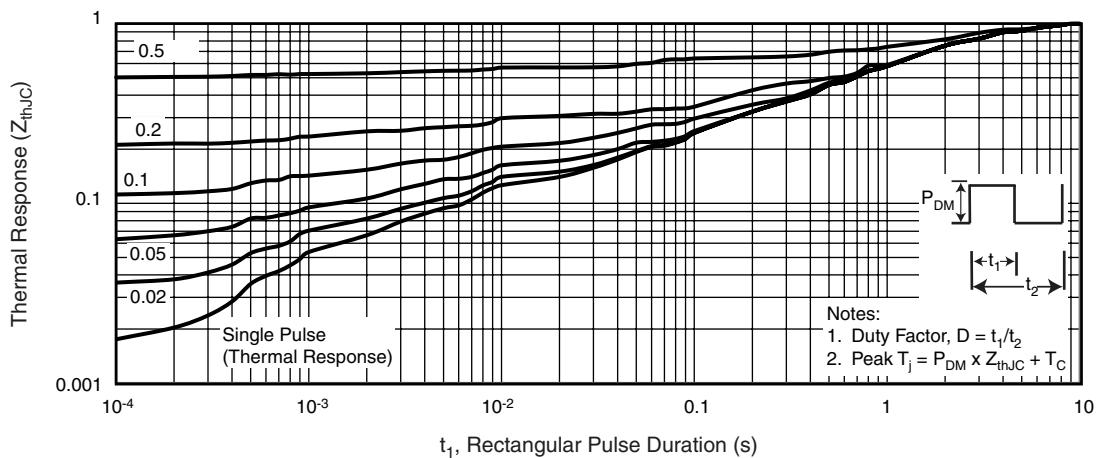
**Fig. 10a - Switching Time Test Circuit**



**Fig. 10b - Switching Time Waveforms**



**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220AB, D<sup>2</sup>PAK)**



**Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220 FULLPAK)**

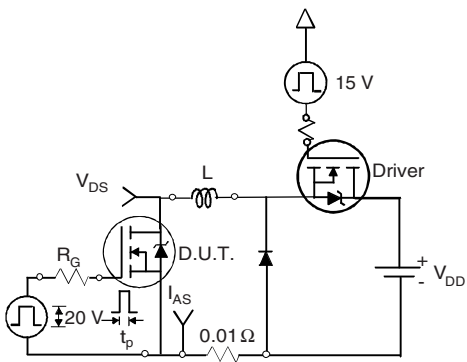


Fig. 13a - Unclamped Inductive Test Circuit

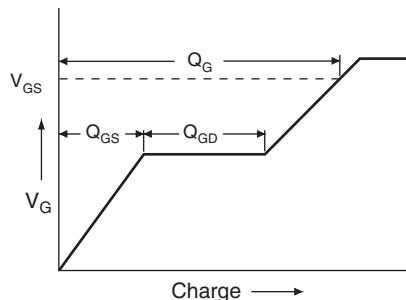


Fig. 14a - Basic Gate Charge Waveform

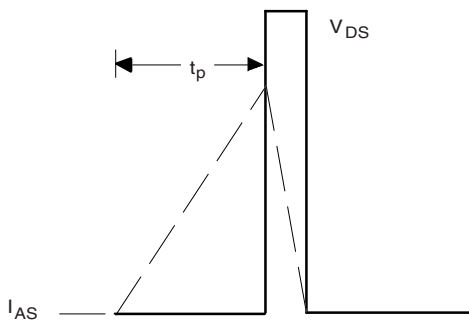


Fig. 13b - Unclamped Inductive Waveforms

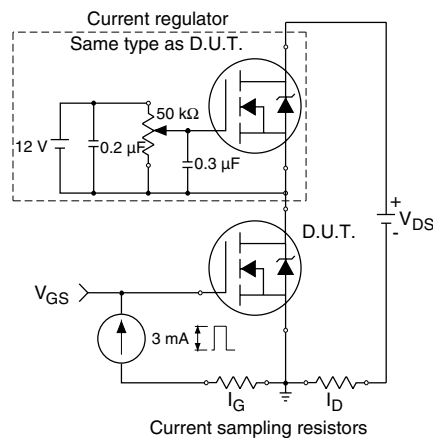
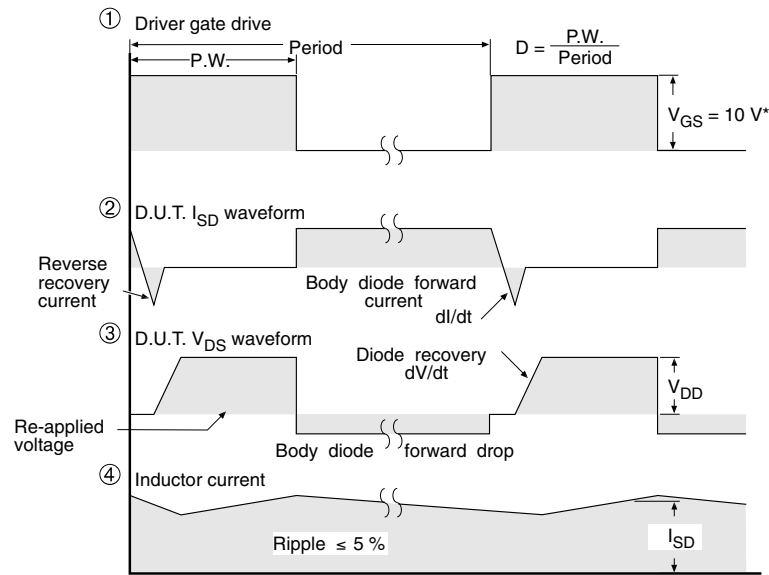
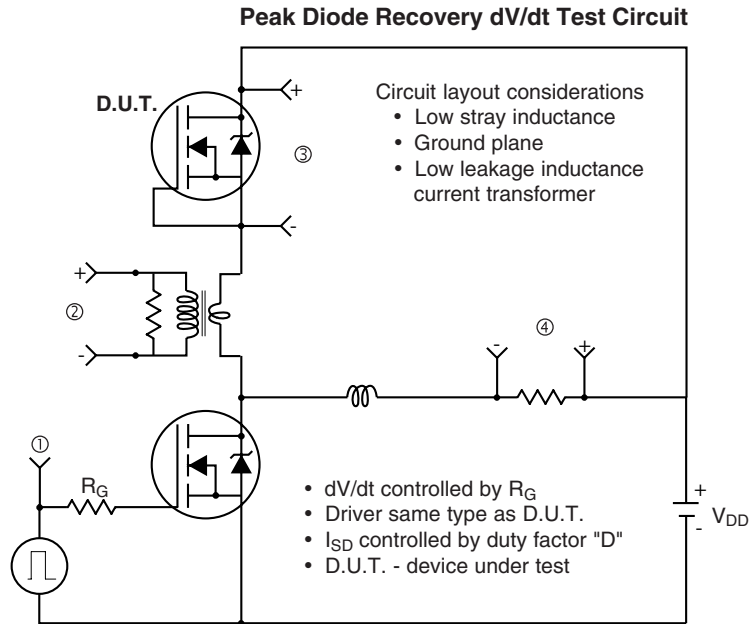


Fig. 14b - Gate Charge Test Circuit



\*  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 15 - For N-Channel**

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